AMENDMENTS TO THE CLAIMS

1. (Currently amended) A power semiconductor module comprising a plurality of semiconductor components situated on substrate regions, wherein

- each substrate region has a top surface and side faces, wherein side faces of two adjacent substrate regions face each other;
- between each two adjacent substrate regions an elastic connecting element is arranged such that the connecting element directly contacts the side faces of the two adjacent substrates, wherein said connecting elements are designed to prevent a deformation of one substrate region to continue to an adjacent substrate region; ~~and~~
- wherein the connecting elements are formed by recesses in a plastic injection-molded module housing enclosing said substrate regions, each recess extending from an exterior of the housing and being arranged between adjacent substrate regions; and
- wherein a thickness of the power semiconductor module is reduced between adjacent substrate regions due to the recesses.

2. (Canceled)

3. (Previously presented) The power semiconductor module as claimed in claim 1, wherein

- the material recesses are slotted.

4. (Previously presented) The power semiconductor module as claimed in claim 1, wherein

- the substrate regions are ceramic.

5. (Previously presented) The power semiconductor module as claimed in claim 1, wherein

- the substrate regions are ceramic.

6-7. (Canceled)

8. (Previously presented) The power semiconductor module as claimed in claim 1, wherein

- the module housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

9. (Previously presented) The power semiconductor module as claimed in claim 3, wherein

- the module housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

10. (Canceled)

11. (Original) The power semiconductor module as claimed in claim 5, wherein

- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

12. (Canceled)

13. (Previously presented) The power semiconductor module as claimed in claim 1, wherein

- the power semiconductor module has a housing, which, in an area between the substrate regions, has action points for a mechanical pressure application of the connecting elements, and
- the housing applies pressure to the individual substrate regions.

14. (Currently amended) A power semiconductor module comprising

- a plurality of substrate elements having top and bottom surface and side walls, each substrate element comprising a semiconductor component arranged on the top surface of a substrate element;
- one or a plurality of elastic connecting elements directly contacting opposing side walls of two adjacent substrate elements, wherein said connecting elements are designed to prevent a deformation of one substrate ~~region~~ element to continue to an adjacent substrate ~~region~~ element;
- a plastic injection-molded module housing enclosing said plurality of substrate elements; ~~and~~
- wherein the connecting elements are formed by recesses in the module housing extending from an exterior of the housing and are arranged between adjacent substrate elements; and
- wherein a thickness of the power semiconductor module is reduced between adjacent substrate elements due to the recesses.

15-16. (Canceled)

17. (Previously presented) The power semiconductor module as claimed in claim 14, wherein

- the material recesses are slotted.

18. (Previously presented) The power semiconductor module as claimed in claim 14, wherein

- the substrate is a ceramic.

19. (Previously presented) The power semiconductor module as claimed in claim 14, wherein

- the module housing, at least in the regions of the substrate elements, is such that it acts on the substrate elements with a spring force.

20. (Previously presented) The power semiconductor module as claimed in claim 14, further comprising

- a heat sink having a flat surface, wherein a bottom surface of the plurality of substrate elements and said plurality of connecting elements are arranged on said flat surface.

21. (Previously presented) The power semiconductor module as claimed in claim 14, wherein

- the module housing in a region between the substrate elements comprises action points for a mechanical pressure application of the connecting elements, and
- the housing applies pressure to the individual substrate elements.

22. (Previously presented) The power semiconductor module as claimed in claim 1, further comprising

- a heat sink having a flat surface, wherein the bottom surface of the plurality of substrate elements and said plurality of connecting elements are arranged on said flat surface.

23. (Currently amended) A power semiconductor module comprising:

- a heat sink having a flat surface,
- a plurality of substrates arranged on the flat surface of the heat sink;
- a plurality of semiconductor components arranged on the substrates,
- one or a plurality of elastic connecting regions in direct contact with adjacent ones of the substrates and arranged directly on the flat surface of the heat sink between adjacent ones of the substrates, wherein the connecting regions are designed to prevent a deformation of one substrate to continue to an adjacent substrate and the connecting regions are formed by recesses in a plastic injection-molded module housing enclosing said ~~substrate regions~~ substrates, each recess extending from an exterior of the housing and being arranged between adjacent substrates, wherein a thickness of the power semiconductor module is reduced between adjacent substrates due to the recesses.

24. (Currently amended) A power semiconductor module, comprising:

a substrate segmented into a plurality of spaced apart substrate regions;

at least one semiconductor component arranged on one or more of the substrate regions;

a plastic injection-molded module housing enclosing said substrate regions and said at least one semiconductor component;

~~a connecting region arranged in the space between adjacent ones of the substrate regions; and~~

connecting regions formed by recesses in the module housing, each recess extending from an exterior of the housing and being arranged between adjacent substrate regions;

wherein the connecting region ~~forms~~ functions as an articulated hinge with each of the adjacent substrate regions so that the adjacent substrate regions can move relative to one another about the articulated hinges; and

wherein a thickness of the power semiconductor module is reduced between adjacent substrate regions due to the recesses.